

# LM3080 Operational Transconductance Amplifier

### **General Description**

The LM3080 is a programmable transconductance block intended to fulfill a wide variety of variable gain applications. The LM3080 has differential inputs and high impedance push-pull outputs. The device has high input impedance and its transconductance ( $g_m$ ) is directly proportional to the amplifier bias current ( $I_{ABC}$ ).

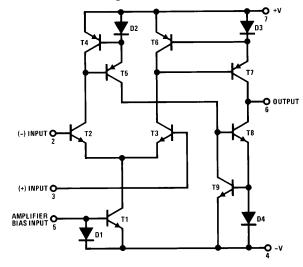
High slew rate together with programmable gain make the LM3080 an ideal choice for variable gain applications such as sample and hold, multiplexing, filtering, and multiplying.

The LM3080N and LM3080AN are guaranteed from 0°C to  $\pm 70$ °C.

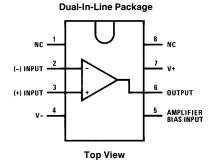
### **Features**

- Slew rate (unity gain compensated): 50 V/µs
- Fully adjustable gain: 0 to g<sub>m</sub> R<sub>L</sub> limit
- Extended g<sub>m</sub> linearity: 3 decades
- Flexible supply voltage range: ±2V to ±18V
- Adjustable power consumption

### **Schematic and Connection Diagrams**



TL/H/7148-1



Order Number LM3080AN, LM3080M or LM3080N See NS Package Number M08A or N08E

Absolute Maximum Ratings
If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (Note 2) LM3080 LM3080A  $\pm\,18V$  $\pm\,22V$ Power Dissipation 250 mW Differential Input Voltage  $\pm\,5V$  Amplifier Bias Current (I<sub>ABC</sub>) DC Input Voltage Output Short Circuit Duration Operating Temperature Range LM3080N or LM3080AN Storage Temperature Range

Lead Temperature (Soldering, 10 sec.)

2 mA  $+V_S$  to  $-V_S$ Indefinite 0°C to +70°C

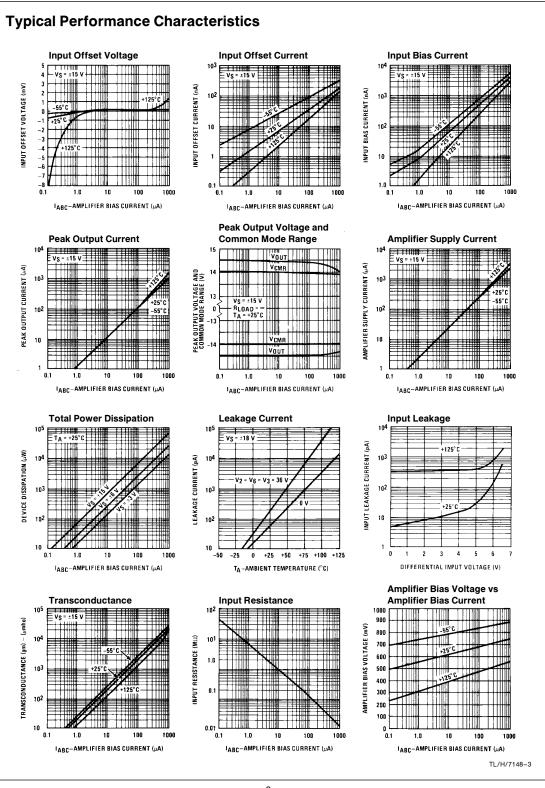
-65°C to +150°C 260°C

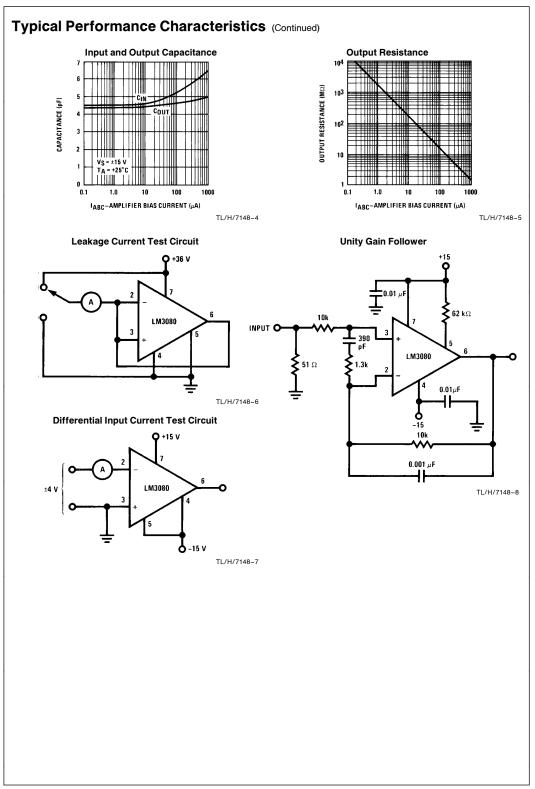
### **Electrical Characteristics** (Note 1)

Parameter	Conditions	LM3080			LM3080A			Units
		Min	Тур	Max	Min	Тур	Max	Julia
Input Offset Voltage	Over Specified Temperature Range $I_{ABC} = 5 \mu A$		0.4	5 6		0.4	2 5 2	mV mV mV
Input Offset Voltage Change	5 μA ≤ I <sub>ABC</sub> ≤ 500 μA		0.1			0.1	3	mV
Input Offset Current	, , , , ,		0.1	0.6		0.1	0.6	μΑ
Input Bias Current	Over Specified Temperature Range		0.4 1	5 7		0.4 1	5 8	μA μA
Forward Transconductance (g <sub>m</sub> )	Over Specified Temperature Range	6700 5400	9600	13000	7700 4000	9600	12000	μmho μmho
Peak Output Current	$\begin{array}{l} {\rm R_L=0,I_{ABC}=5\mu A} \\ {\rm R_L=0} \\ {\rm R_L=0} \\ {\rm OverSpecifiedTemperatureRange} \end{array}$	350 300	5 500	650	3 350 300	5 500	7 650	μΑ μΑ μΑ
Peak Output Voltage Positive Negative	$\begin{aligned} R_L &=  \infty, 5 \; \mu A \leq I_{ABC} \leq 500 \; \mu A \\ R_L &=  \infty, 5 \; \mu A \leq I_{ABC} \leq 500 \; \mu A \end{aligned}$	+ 12 - 12	+ 14.2 - 14.4		+12 -12	+ 14.2 - 14.4		V V
Amplifier Supply Current			1.1			1.1		mA
Input Offset Voltage Sensitivity Positive Negative	$\Delta V_{OFFSET}/\Delta V + \Delta V_{OFFSET}/\Delta V -$		20 20	150 150		20 20	150 150	μV/V μV/V
Common Mode Rejection Ratio		80	110		80	110		dB
Common Mode Range		±12	±14		±12	±14		V
Input Resistance		10	26		10	26		kΩ
Magnitude of Leakage Current	I <sub>ABC</sub> = 0		0.2	100		0.2	5	nA
Differential Input Current	$I_{ABC} = 0$ , $I_{ABC} = \pm 4V$		0.02	100		0.02	5	nA
Open Loop Bandwidth			2			2		MHz
Slew Rate	Unity Gain Compensated		50			50		V/μs

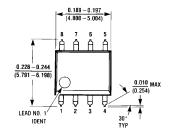
Note 1: These specifications apply for  $V_S = \pm 15V$  and  $T_A = 25^{\circ}C$ , amplifier bias current (I<sub>ABC</sub>) = 500  $\mu$ A, unless otherwise specified.

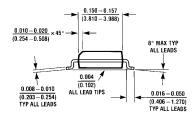
Note 2: Selection to supply voltage above  $\pm 22 \text{V},$  contact the factory.

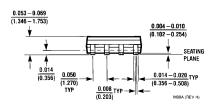




## Physical Dimensions inches (millimeters)

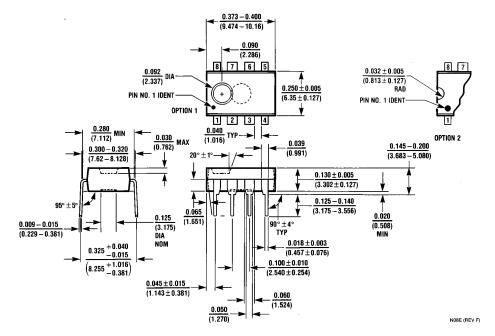






Molded Package SO (M) Order Number LM3080M NS Package Number M08A

## Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N) Order Number LM3080AN or LM3080N **NS Package Number N08E** 

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